NCE N-Channel Super Trench Power MOSFET

Description

The NCEP85T25VD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS}(\text{ON})}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

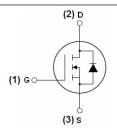
General Features

- V_{DS} =85V, I_{D} =250A $R_{DS(ON)}$ <2.0m Ω @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

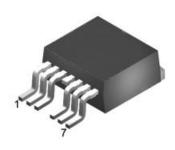
100% UIS TESTED! 100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-263-7L top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-------------|----------------|-----------|------------|----------|
| NCEP85T25VD | NCEP85T25VD | TO-263-7L | - | - | - |

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|------------------------|------------|------|
| Drain-Source Voltage | V _{DS} | 85 | V |
| Gate-Source Voltage | V _G s | ±20 | V |
| Drain Current-Continuous | I _D | 250 | А |
| Drain Current-Continuous(T _C =100 ℃) | I _D (100°C) | 180 | Α |
| Pulsed Drain Current | I _{DM} | 1000 | А |
| Maximum Power Dissipation | P _D | 300 | W |
| Derating factor | | 2 | W/℃ |
| Single pulse avalanche energy (Note 1) | E _{AS} | 2000 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 175 | °C |

Thermal Characteristic

| Thermal Resistance,Junction-to-Case | Rejc | 0.5 | °C/W |
|-------------------------------------|------|-----|------|
|-------------------------------------|------|-----|------|

NCEP85T25VD

Electrical Characteristics (T_C=25°C unless otherwise noted)

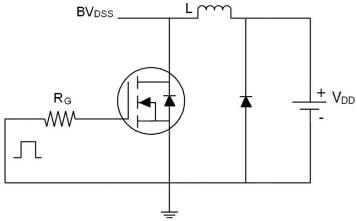
| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|--|-----|-------|------|------|
| Off Characteristics | | | | | | , |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250µA | 85 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =85V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS},I_{D}=250\mu A$ | 2.5 | 3.5 | 4.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =100A | - | 1.7 | 2.0 | mΩ |
| Forward Transconductance | g FS | V _{DS} =10V,I _D =100A | - | 90 | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{lss} | V 40V/V 0V/ | - | 10700 | - | PF |
| Output Capacitance | Coss | V_{DS} =40V, V_{GS} =0V, | - | 1700 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | - | 76 | - | PF |
| Switching Characteristics (Note 2) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V_{DD} =40V, I_{D} =100A V_{GS} =10V, R_{G} =1.6 Ω | - | 28 | - | nS |
| Turn-on Rise Time | t _r | | - | 73 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 86 | - | nS |
| Turn-Off Fall Time | t _f | | - | 33 | - | nS |
| Total Gate Charge | Qg | \/ -40\/ L -400A | - | 142 | | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =40V,I _D =100A, | - | 56 | | nC |
| Gate-Drain Charge | Q _{gd} | V _{GS} =10V | - | 24 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V,I _F = I _S | - | | 1.2 | V |
| Diode Forward Current | Is | | - | - | 250 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = I _S | - | 115 | | nS |
| Reverse Recovery Charge | Qrr | $di/dt = 100A/\mu s$ | - | 320 | | nC |

Notes:

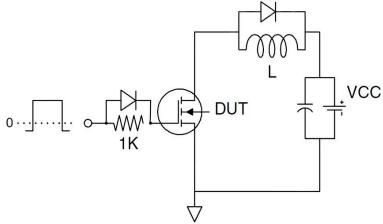
- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=40V,VG=10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Test Circuit

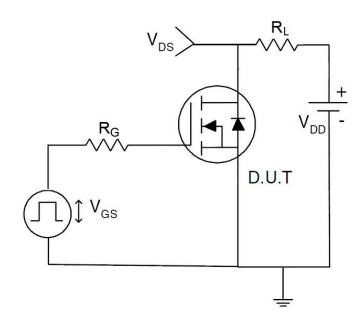
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





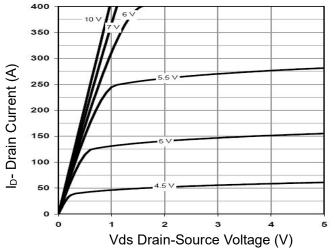


Figure 1 Output Characteristics

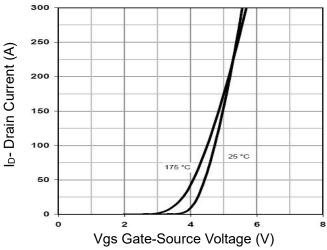


Figure 2 Transfer Characteristics

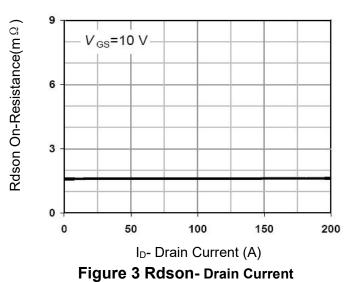


Figure 4 Rdson-JunctionTemperature

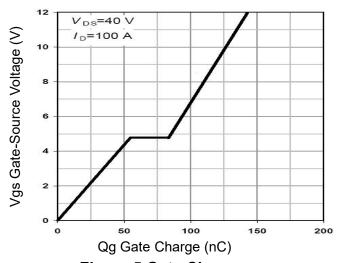


Figure 5 Gate Charge

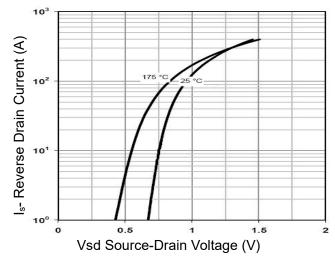
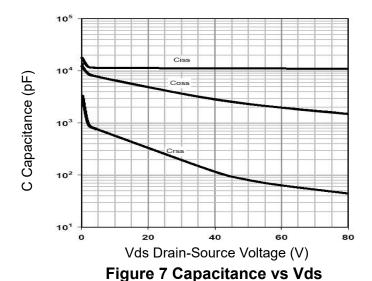


Figure 6 Source- Drain Diode Forward



W) 250

Loiped 200

150

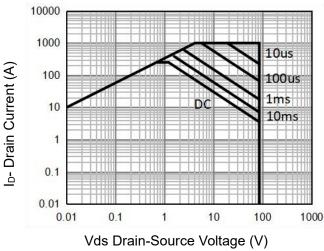
100

50

Ta-Junction Temperature(°C)

300

Figure 9 Power De-rating



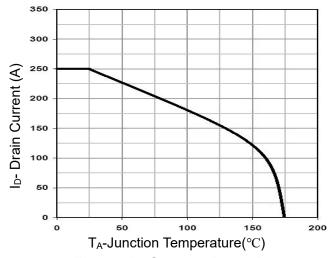


Figure 8 Safe Operation Area (Note 3)

Figure 10 Current De-rating

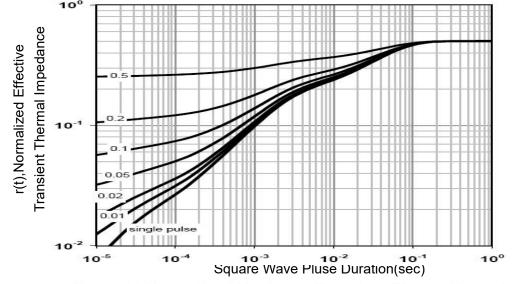
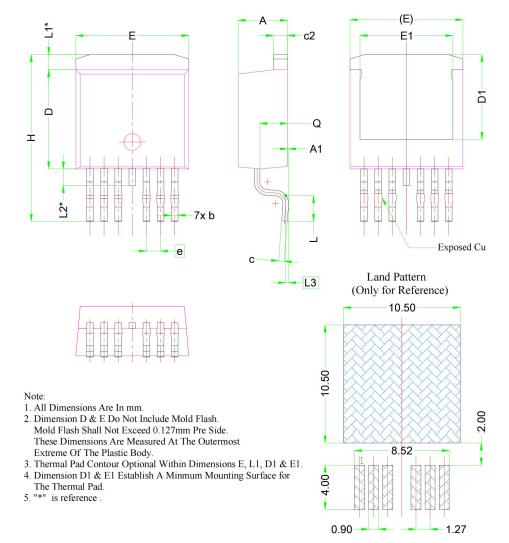


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-7L Package Information



| SYMBOL | DIMENSIONS | | | | |
|----------|------------|-------|-------|--|--|
| STIVIBUL | MIN. | NOM. | MAX. | | |
| Α | 4.24 | 4.44 | 4.64 | | |
| A1 | 0.00 | 0.10 | 0.25 | | |
| b | 0.50 | 0.60 | 0.70 | | |
| С | 0.40 | 0.50 | 0.60 | | |
| c2 | 1.15 | 1.27 | 1.40 | | |
| D | 8.82 | 8.92 | 9.02 | | |
| D1 | 6.86 | 7.65 | | | |
| E | 9.96 | 10.16 | 10.36 | | |
| E1 | 8.20 | 8.35 | 8.50 | | |
| е | 1.27 BSC | | | | |
| Н | 14.61 | 15.00 | 15.88 | | |
| L | 1.78 | 2.32 | 2.79 | | |
| L1 | 1.36 REF. | | | | |
| L2 | 1.50 REF. | | | | |
| L3 | 0.25 BSC | | | | |
| Q | 2.30 | 2.48 | 2.70 | | |

NCEP85T25VD

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